Abstracts

30-V MMIC Power Amplifier with Novel Bias Circuitry

K.E. Peterson, H.-L.A. Hung, F.R. Phelleps, E.Y. Chang, J.L. Singer, H.E. Carlson and A.B. Cornfeld. "30-V MMIC Power Amplifier with Novel Bias Circuitry." 1991 MTT-S International Microwave Symposium Digest 91.2 (1991 Vol. II [MWSYM]): 823-826.

High-voltage power amplifiers allow more efficient DC power conditioning and distribution than is possible with low-voltage systems. Results are presented for the first fully monolithic High-Voltage FET amplifier, with on-chip power combining and novel bias circuitry. Output power greater than 2 W was obtained with 30-V drain bias at 11 GHz. A power-added efficiency of 34 percent was also achieved, which is believed to be the best reported for such amplifiers.

❑ Return to main document.